

JP2003338629

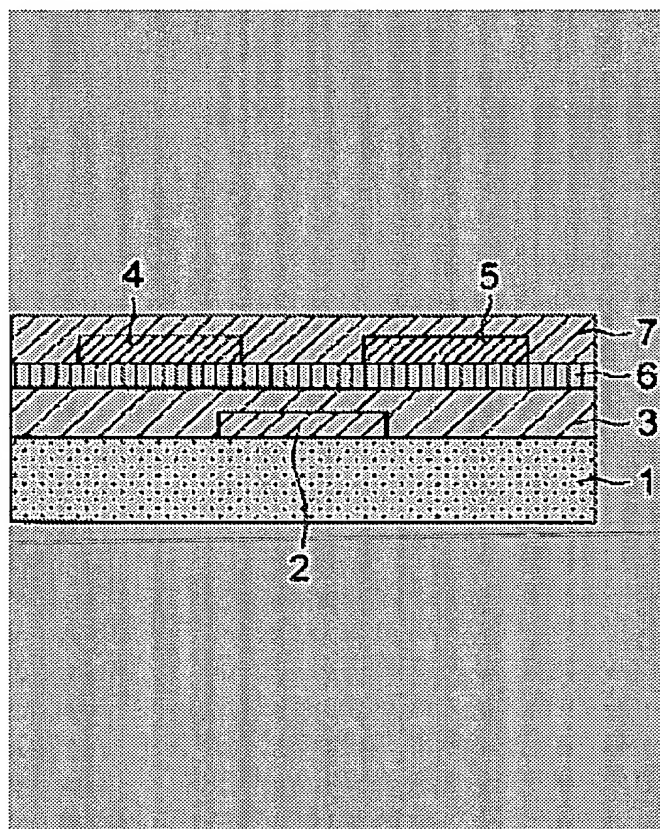
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Abstract of JP2003338629

<P>PROBLEM TO BE SOLVED: To provide an organic thin-film transistor that is stably activated under an environment wherein a device is used. **<P>SOLUTION:** In the organic thin-film transistor having a gate electrode 2 formed on a support 1, a gate insulating layer 3 for covering the gate electrode, a source electrode 4, a drain electrode 5, and an organic semiconductor layer 6 formed on the gate insulating layer, at least the organic semiconductor layer is sealed with a sealing film 7 made of an ethylene-vinyl alcohol copolymer, thus achieving the organic thin-film transistor having a low leakage current and superior switching characteristics with a high ON/OFF ratio under high humidity.

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